

## Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFETs

PRODUCT SUMMARY							
N-CHANNEL 1 N-CHANNEL							
V <sub>DS</sub> (V)	40	40					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.022	0.011					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.026	0.013					
I <sub>D</sub> (A)	15	45					
Configuration	Dual N						

#### **FEATURES**

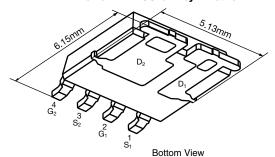
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>d</sup>
- 100 % R<sub>a</sub> and UIS Tested
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

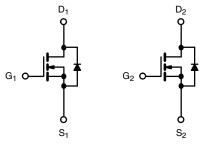




ROHS COMPLIANT HALOGEN FREE

#### PowerPAK® SO-8L Asymmetric





N-Channel 1 MOSFET

N-Channel 2 MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L Dual Asymmetric
Lead (Pb)-free and Halogen-free	SQJ942EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub>	= 25 °C, unless	otherwise n	oted)			
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	40	40	V	
Gate-Source Voltage		$V_{GS}$	±	V		
Continuous Drain Currenta	T <sub>C</sub> = 25 °C		15	45		
Continuous Drain Current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	15	32		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	15	44	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	60	180		
Single Pulse Avalanche Current			19	27		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	18.5	36.5	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	В	17	48	W	
Maximum Fower Dissipation	T <sub>C</sub> = 125 °C	$P_{D}$	6	16	VV	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175		00		
Soldering Recommendations (Peak Temperature)e, f		20	60	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	75	70	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	9	3.1	C/VV

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Static		l e e e e e e e e e e e e e e e e e e e							
Davis Os and Baral day of Wallace	.,	V <sub>GS</sub> =	N-Ch 1	40	-	-			
Drain-Source Breakdown Voltage	$V_{DS}$	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	N-Ch 2	40	-	-	,,	
Oala Oa aa Thaalal Wallaca	.,	V <sub>DS</sub> =	N-Ch 1	1.3	1.8	2.3	V		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	N-Ch 2	1.3	1.8	2.3		
Cata Cauraa Laakaaa			0.1/.1/	N-Ch 1	-	-	± 100		
Gate-Source Leakage	I <sub>GSS</sub>	v <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	N-Ch 2	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> 40 V	N-Ch 1	-	-	1		
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 40 V	N-Ch 2	-	-	1		
Zana Onto Vallence Burin On and		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	N-Ch 1	-	-	50	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	N-Ch 2	-	-	50	μA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	N-Ch 1	-	-	150		
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	N-Ch 2	-	-	150		
0.01.0.10		V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	N-Ch 1	30	-	-	_	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	N-Ch 2	30	-	-	A	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 7.8 A	N-Ch 1	-	0.018	0.022		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10.1 A	N-Ch 2	-	0.009	0.011	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 7.8 A, T <sub>J</sub> = 125 °C	N-Ch 1	-	-	0.032		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10.1 A, T <sub>J</sub> = 125 °C	N-Ch 2	-	-	0.017		
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 7.8 A, T <sub>J</sub> = 175 °C	N-Ch 1	-	-	0.038		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10.1 A, T <sub>J</sub> = 175 °C	N-Ch 2	-	-	0.020		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 7.1 A	N-Ch 1	-	0.022	0.026		
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 9.3 A	N-Ch 2	-	0.011	0.013	1	
			= 15 V, I <sub>D</sub> = 7.8 A	N-Ch 1	-	46	-		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> =	: 15 V, I <sub>D</sub> = 10.1 A	N-Ch 2	-	73	-	S	
Dynamic <sup>b</sup>									
	_	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, f = 1 MHz	N-Ch 1	-	647	809		
Input Capacitance	$C_{iss}$	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, f = 1 MHz	N-Ch 2	-	1161	1451	-	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, f = 1 MHz	N-Ch 1	-	105	131	_	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, f = 1 MHz	N-Ch 2	-	178	222	pF	
	_	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, f = 1 MHz	N-Ch 1	-	42	53		
Reverse Transfer Capacitance	$C_{rss}$	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V, f = 1 MHz	N-Ch 2	-	68	85		
		V <sub>GS</sub> = 10 V	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 16 A	N-Ch 1	_	13.1	19.7		
Total Gate Charge <sup>c</sup>	$Q_g$	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 6 \text{ A}$	N-Ch 2	_	22.5	33.8	-	
	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 16 A	N-Ch 1	_	2.12	-	nC	
Gate-Source Charge <sup>c</sup>		V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 6 \text{ A}$	N-Ch 2	-	3.35	-		
	Q <sub>gd</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 16 \text{ A}$	N-Ch 1	-	1.84	-	-	
Gate-Drain Charge <sup>c</sup>		$V_{GS} = 10 \text{ V}$ $V_{DS} = 20 \text{ V}, I_D = 6 \text{ A}$		N-Ch 2	_	3.14	-	-	
		f = 1 MHz		N-Ch 1	1.5	3.02	5		
Gate Resistance	$R_g$			N-Ch 2	2.05	4.11	7	Ω	

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.



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<b>SPECIFICATIONS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT		
Turn-On Delay Time <sup>c</sup>		$\begin{aligned} V_{DD} &= 20 \text{ V}, \text{ R}_L = 20 \Omega\\ I_D &\cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega \end{aligned}$	N-Ch 1	-	33	50			
	t <sub>d(on)</sub>	$\begin{aligned} &V_{DD}=20 \text{ V, } R_L=20 \Omega\\ &I_D\cong 1 \text{ A, } V_{GEN}=10 \text{ V, } R_g=1 \Omega \end{aligned} \qquad \text{N-Ch}$		-	40	60			
Rise Time <sup>c</sup>	+	$\begin{aligned} V_{DD} &= 20 \text{ V}, \text{ R}_L = 20 \Omega\\ I_D &\cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega \end{aligned}$	N-Ch 1	i	25	38			
nise Tillle	t <sub>r</sub>	$\begin{aligned} V_{DD} &= 20 \text{ V}, \text{ R}_L = 20 \Omega\\ I_D &\cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega \end{aligned}$	N-Ch 2	i	31	46	ns		
Turn Off Doloy Times		$\begin{aligned} V_{DD} &= 20 \text{ V}, \text{ R}_L = 20 \Omega\\ I_D &\cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega \end{aligned}$	N-Ch 1	ı	29	43			
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\begin{aligned} V_{DD} &= 20 \text{ V}, \text{ R}_L = 20 \Omega\\ I_D &\cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega \end{aligned}$	N-Ch 2	-	52	78	3		
Fall Times		$\begin{aligned} V_{DD} &= 20 \text{ V}, \text{ R}_L = 20 \Omega\\ I_D &\cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega \end{aligned}$	N-Ch 1	-	12	18			
Fall Time <sup>c</sup>	t <sub>f</sub>	$\begin{aligned} V_{DD} &= 20 \text{ V}, \text{ R}_L = 20 \Omega\\ I_D &\cong 1 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega \end{aligned}$	N-Ch 2	-	16	24			
Source-Drain Diode Ratings and Characteristics <sup>b</sup>									
Pulsed Current <sup>a</sup>	la		N-Ch 1	ı	-	60	Α		
i dised Guirent	I <sub>SM</sub>		N-Ch 2	1	-	180			
Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 5.2 A	N-Ch 1	ı	0.8	1.2	V		
		$I_{S} = 6.8 \text{ A}$	-	0.8	1.2	]			

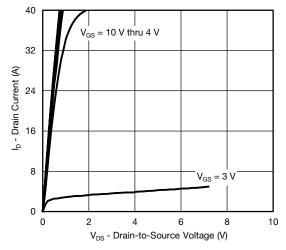
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

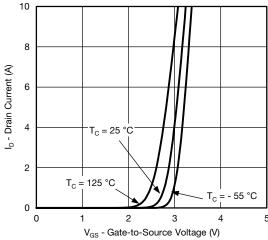
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



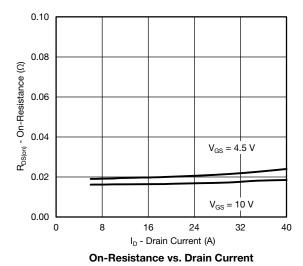
### **N-CHANNEL 1 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

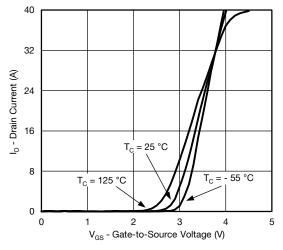


#### **Output Characteristics**

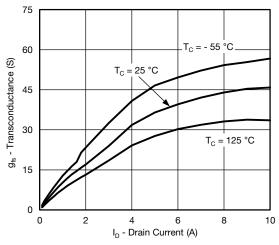


Transfer Characteristics

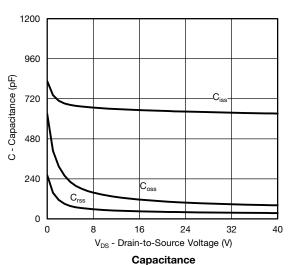




**Transfer Characteristics** 

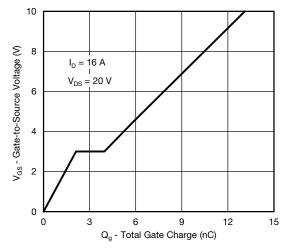


Transconductance

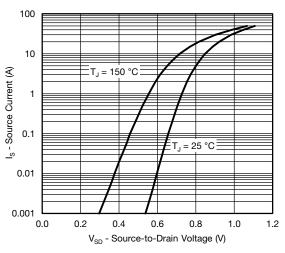




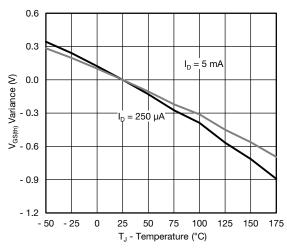
### **N-CHANNEL 1 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



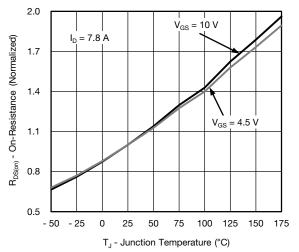
#### **Gate Charge**



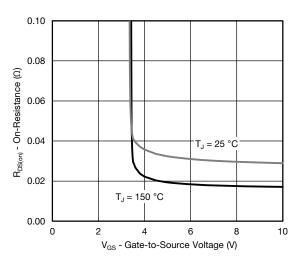
#### **Source Drain Diode Forward Voltage**



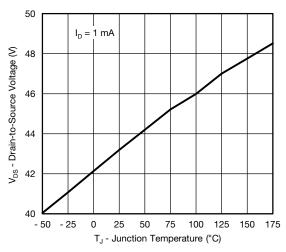
**Threshold Voltage** 



On-Resistance vs. Junction Temperature

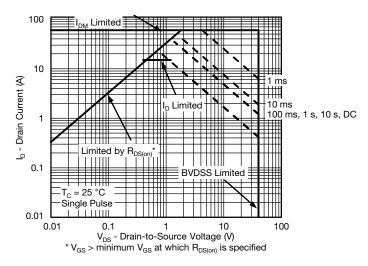


On-Resistance vs. Gate-to-Source Voltage

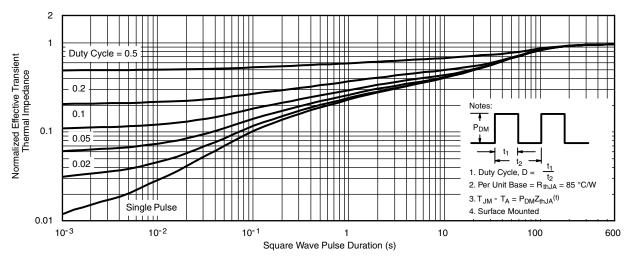


Drain Source Breakdown vs. Junction Temperature

### **N-CHANNEL 1 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



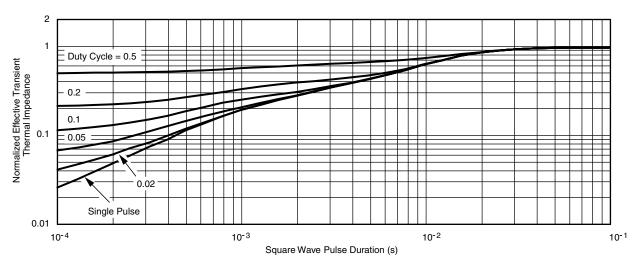
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

### **N-CHANNEL 1 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

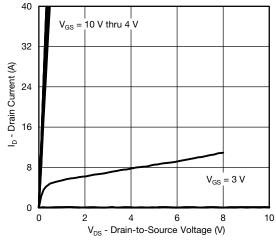
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions.

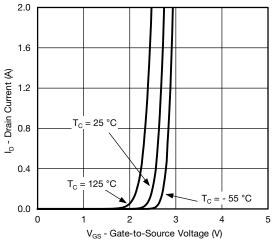
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities



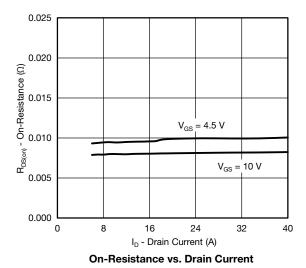
### **N-CHANNEL 2 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

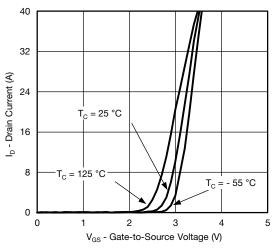


#### **Output Characteristics**

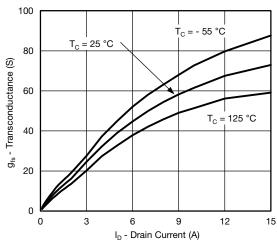


**Transfer Characteristics** 

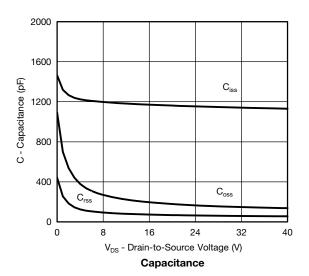




**Transfer Characteristics** 

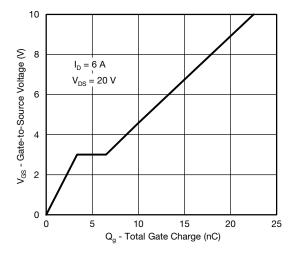


Transconductance

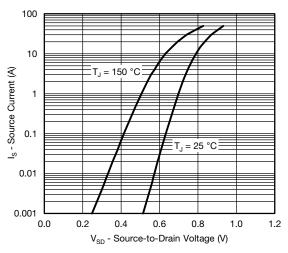




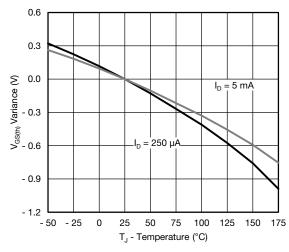
### **N-CHANNEL 2 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



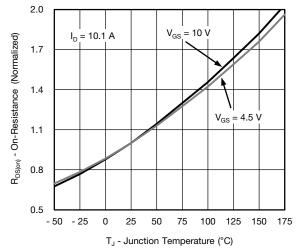
#### **Gate Charge**



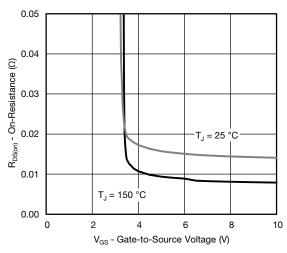
#### **Source Drain Diode Forward Voltage**



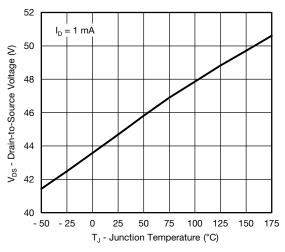
**Threshold Voltage** 



On-Resistance vs. Junction Temperature



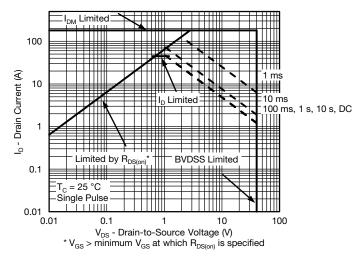
On-Resistance vs. Gate-to-Source Voltage



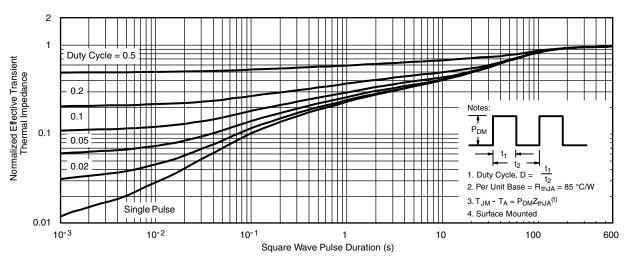
Drain Source Breakdown vs. Junction Temperature



### **N-CHANNEL 2 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

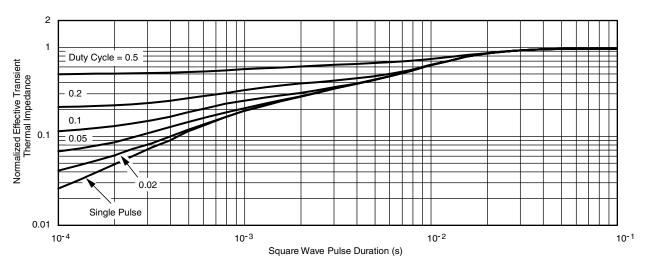


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

### **N-CHANNEL 2 TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

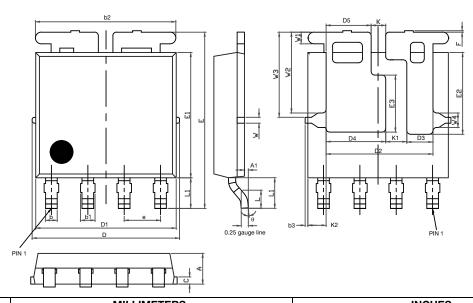
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62669">www.vishay.com/ppg?62669</a>.



# PowerPAK® SO-8L Assymetric Case Outline



DIM.	MILLIMETERS			INCHES				
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	0.06	0.13	0.000	0.003	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3	0.04	0.12	0.20	0.002	0.005	0.008		
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.63	3.73	3.83	0.143	0.147	0.151		
D3	0.81	0.91	1.01	0.032	0.036	0.040		
D4	1.98	2.08	2.18	0.078	0.082	0.086		
D5	1.47	1.57	1.67	0.058	0.062	0.066		
е	1.20	1.27	1.34	0.047	0.050	0.053		
Е	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
E3	1.89	1.99	2.09	0.074	0.078	0.082		
F	0.05	0.12	0.19	0.002	0.005	0.007		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K	0.41	0.51	0.61	0.016	0.020	0.024		
K1	0.64	0.74	0.84	0.025	0.029	0.033		
K2	0.54	0.64	0.74	0.021	0.025	0.029		
W	0.13	0.23	0.33	0.005	0.009	0.013		
W1	0.31	0.41	0.51	0.012	0.016	0.020		
W2	2.72	2.82	2.92	0.107	0.111	0.115		
W3	2.86	2.96	3.06	0.113	0.117	0.120		
W4	0.41	0.51	0.61	0.016	0.020	0.024		
θ	5°	10°	12°	5°	10°	12°		

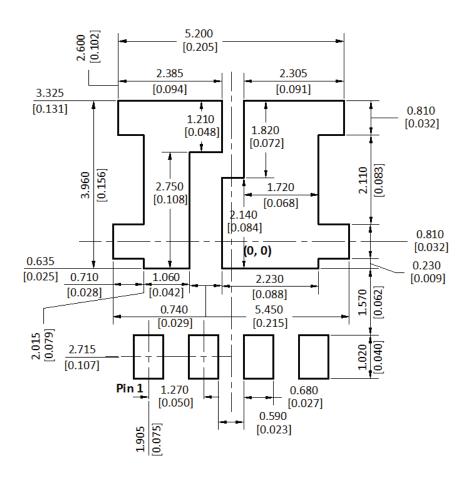
DWG: 6009

#### Note

• Millimeters will govern



#### RECOMMENDED MINIMUM PADs FOR PowerPAK® SO-8L DUAL ASYMMETRIC



Recommended Minimum Pads Dimensions in mm [inches]



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